Phase Diagram for Quantum Hall Bilayers at = 1

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We present a phase diagram for a double quantum well bilayer electron gas in the quantum H all regime at total lling factor = 1, based on exact numerical calculations of the topological C hern number matrix and the (inter-layer) super uid density. We nd three phases: a quantized H all state with pseudo-spin super uidity, a quantized H all state with pseudo-spin \gauge-glass" order, and a decoupled composite Ferm i liquid. C om parison with experiments provides a consistent explanation of the observed quantum H all plateau, H all drag plateau and vanishing H all drag resistance, as well as the zero-bias conductance peak e ect, and suggests some interesting points to pursue experimentally.

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The coexistence of an incom pressible integer quantum Halle ect (IQHE) state and interlayer super uidity has been established through a series of experimental and theoreticalworks on bilayer two dimensional electron system s at a total electron lling num ber = $1^{2,3,4}$. Such an IQHE is a consequence of the strong Coulomb interactions, which lead to a charge gap at = 1. Denoting the layer index as pseudospin \up" and \down", the ground state is a quantum ferrom agnet with spontaneous interlayer phase coherence^{5,6}, which exhibits super uidity in the zero layer separation $\lim it, d = 0.0$ n the other hand, in the d ! 1 limit, the two layers are decoupled, each com prising a com pressible com posite ferm ion liquid at = 1=2. The nature of the phases and transitions^{7,8,9,10,11} between these two lim its has attracted many recent studies. A generalized pseudospin description suggests a rst order transition⁸ at which the pseudospin order vanishes upon increasing d. The relation of the loss of ferrom agnetism with the disappearance of the IQHE remains unclear, and indeed several scenarios in which the ferrom agnetism and IQ HE do not vanish simultaneously have also been proposed based on the Chem-Sim ons mean-eld theory. Furtherm ore, in real samples with impurities, a rst order transition is believed to be impossible on general grounds¹². A consistent picture for the phase transitions is still absent.

Fundamentally, the distinct phases of the system at T = 0 are characterized by their topological order and/or broken symmetries. Experimentally, these are predominantly rejected in electrical transport coeccients, particularly the H all conductance. Due to the lack of exact solutions (except at d = 0 without in purities), the ground state phases and transport properties have mainly been discussed based on electric theories^{7,9}. Exact numerical calculations for these systems have been done in the absence of random disorder potential^{10,11}, which cannot provide direct information about the transport. In this letter, we report the rst nite-size exact calculations of transport properties for such a system in the presence of random in purities, by obtaining the topological Chem

num ber m atrix of the m any-body wavefunction and the super uid density of the ground state.

The Chern num ber^{13,14} is a unique integer topological invariant associated with a wavefunction, and can be used to distinguish di erent quantum Hall states. Physically, the Chem number equals the boundary condition averaged Hallconductance (in units of e²=h), so an IQ HE state is expected to display a xed non-zero integer C hem num ber independent of disorder con gurations. A state with a non-quantized Hall conductance instead displays a random integer Chern num ber intrinsically uctuating with di erent disorder con gurations or other external param eters. Such states are generally expected to be critical or uid in nature, since a nonzero current^{4,15} necessarily exists in the bulk to destroy the exact quantization of Hall conductance. Thus the distribution of Chern numbers over samples also reveals the extended or localized character of the state.

N um erical calculations of the Chem num ber have up to now only been carried out from single-particle wavefunctions in non-interacting system $s^{14,15}$. The Chem num ber of a many-body wavefunction is, nevertheless, well-de ned, albeit di cult to calculate. We have developed a new approach to obtain the exact Chem num ber by num erically evaluating the Berry phase of the many-body wavefunction upon changing boundary phases adiabatically¹⁶. In the present bilayer system the topological Chem num bers form a 2 2 m atrix related to the topological ordering of the system ¹⁷, which determ ines the charge and spin (we will refer pseudospin as spin) H all conductances (as well as the H all drag, which is the di erence of the two).

Our main results can be summarized as a numerical phase diagram (see Fig. 1) in the d W plane (W is the disorder strength) with three distinguishable phases. Phase I is the usual bilayer ferrom agnet, embodying coexistence of the = 1 IQ HE and inter-layer super uidity, occurring at small d and W . At relatively strong W but small d regime, the super uid state will rst undergo a phase transition to a \gauge glass" (phase II), in

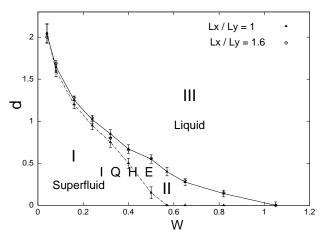


FIG.1: The solid line is the critical layer separation $d_{\rm c}$ vs. W , which separates the IQHE plateau (phase I and II) from the composite Ferm i liquid state (phase III). The dashed line is the critical $d_{\rm s}$ vs. W , which separates the super uid state (phase I) from the gauge glass state (phase II).

which n_s vanishes due to strong phase frustration. Both phases I and II have the same Chern number matrix: a uniquely quantized charge Chern number $C^{c} = 1$ and a random spin Chern number, which result in nonzero Hall drag conductance. In phase I, spin super uidity implies that the full spin resistivity tensor and hence $_{xy}^{s}$ vanishes below the K osterlitz-T houless tem perature, so we expect quantization of the Hall drag resistance, $d_{xy} = c_{xy} = h = e^2$ with exponentially small therm ally activated corrections at low tem perature. Phase II, despite having the sam e Chern num ber m atrix as phase I, has a di erent behavior of the spin resistivity, since the average n_s vanishes. Conventional theory for the gauge glass carried over to this problem suggests⁵ $\frac{s}{x}$. хx are exponentially sm all but non-zero at any T > 0 and vanish only at T = 0, leading to a weaker quantization of the Halldrag resistance. W ith the increase of d or W, phase II undergoes a transition to the com pressible Ferm i liquid (phase III). Phase III can be understood from the large d lim it of decoupled layers. It is a metallic state, characterized by zero drag conductance and a nite diagonal longitudinal conductance. These results provide a consistent understanding for the existing experiments (see below).

In the presence of a strong m agnetic eld, the H am iltonian, projected onto the lowest Landau level, for a double layer two-dimensional electron gas can be written as:

$$H = \begin{cases} X & X \\ e^{q^{2}=2}V ; (q)e^{iq (R_{i} R_{j})} \\ X & X \\ e^{q^{2}=4}V_{im p} (q)e^{iq R_{i}} \\ i; q \in 0 \end{cases}$$
(1)

where R_i is the coordinate of the i-th electron in layer (=1; 1).V; (q) = 2 e²=(qL_xL_y) exp(qd;), is the C oulom b potential. $V_{im p}(q)$ is the impurity potential generated according to the correlation relation < $V_{im p}(q)V_{im p}(q) > = \frac{W^2}{L_xL_y}$; q_{iq^0} , which corresponds

to < $V_{\rm im\ p}\ (r)V_{\rm im\ p}\ (r^0)$ >= W 2 ; (r $r^0)$ in real space, where W is the strength of the disorder. We set the magnetic length ' = 1 and the interaction strength e^2 = ' = 1 for convenience. We impose the generalized boundary conditions: T $(L_j)j$ >= e^{i} j > (j = x;y), to the nite size double layer system, each in an L_k L_y rectangular cell with an integer number of ux quanta N $_s$ = $L_x L_y$ =2 . T (r) is the many-body magnetic translation operator. The tunneling term is not considered here in order to study the interesting limit where the correlation between two layers is purely due to C oulom b interaction. We consider up to N $_e$ = 12 electrons at lling number = N_e =N $_s$ = 1, spanning a Hilbert space of size N $_{\rm basis}$ = 853776.

Through a unitary transformation = $\sum_{i=1}^{P} \sum_{i=1}^{N_{e}} \left(\frac{x}{L_{x}} x_{i} + \frac{y}{L_{y}} y_{i} \right) \right], \text{ the topological}$ Chem num ber^{13,15} can be calculated as:

$$C' = \frac{i}{4} d_{j}fh = \frac{i}{2} h_{j}gh = \frac{i}{$$

where j has layer index and with j = x; y.W ith j = 1; 1, C i form s a 2 2 matrix. The closed path integral is along the phase boundary of the 2 2 unit cell. If common or opposite boundary phases are opposed on the two layers, then one obtains charge and spin Chern number, $C^{c,s}$, which is related to the boundary phase averaged charge and spin H all conductances $\frac{c,s}{xy} = C \frac{c,s}{h}$, respectively. We separate the phase space into a mesh of 64-200 squares. By repeatedly calculating wavefunctions at all nodes of the mesh using Lanczos method, we determ ine the integer Chern number for the many-body state in each disorder con guration.

We rst consider the charge Chern number C^c as a function of d. At a weak disorder strength W = 0.16and d < 1, we nd $C^c = 1$ for all disorder samples at $N_e = 6;8;10;11$ and 12 (20 sam ples for $N_e = 12$ and 1000 for N $_{\rm e}$ = 6). Hence the corresponding ground state displays the IQ HE with total (charge) Hall conductance $c_{xy} = \frac{e^2}{h}$. As we further increase d, a strong uctuation of the Chern number takes place at d 1:1 1:3, which are caused by level crossings upon tuning the boundary phases and disorder. The persistence of the crossing of low energy states at particular values of d; W is a signature of a quantum phase transition, and is associated with the collapse of the mobility gap. Thus the mobility of the state in the charge channel is tied to the uctuations of $C^{c14,15}$, motivating us to de ne ext = P ($C^{c} \in 1$) (the probability of nding $C^{c} \in 1$) as a characterization of the extensiveness of the many-body state. If ext extrapolates to a nonzero value in the therm odynam ic lim it, it represents a uid phase which can carry current in the bulk to spoil the exact quantization of c_{xy}^{c} .

To determ ine the critical d_c for the = 1 IQHE to metal transition, we plot _{ext} as a function of d at W = 0.16, N_e = 6, 10 and 11 in Fig 2. _{ext} always increases rapidly around d 1.1 1.3 and saturates to 0.5 at larger d. In the same gure, we plot _{ext} = d (d = 0.05) as

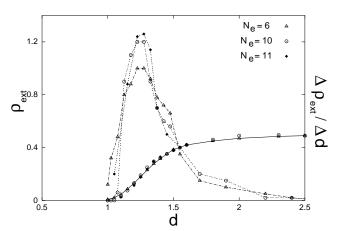


FIG. 2: The elective charge mobility $_{ext}$ at W = 0.16, de ned as the ratio of the number of sam ples with C[°] \notin 1 and the total number of sam ples, as a function of d at N_e = 6, 10 and 11. $_{ext}$ = d vs. d is also shown.

a function of d. A round d = 1.25, there is always a very strong peak growing with N_e. We determ ine the critical layer separation d_c (= 1.25 0.05 for W = 0.16) for the IQ HE to metaltransition by the location of the maximum of this peak for each W . A step jump of $_{ext}$ is expected for such a transition in the therm odynam ic limit.

The critical d_c as a function of W determ ined in this manner is indicated in Fig. 1 by the solid line. The d_c for two aspect ratios ($L_x=L_y = 1$ and 1:6) agree well with each other, demonstrating the sm allness of overall

nite size e ects. At W ! 0, gl saturates to around $d_c = 2.2$ 0.2 with relatively large error bars due to increasing nite-size e ects at very weak W (at W = 0.04, $d_c = 2.02$ 0.13). We note that studies based on the local ferrom agnetic m om ent m_{FM} for weak disorder will tend to underestim ate d_c , due to a large reduction of m_{FM} by low energy states mixing around d 1.5, which, how ever, does not a ect the Chern number.

M ore information on the nature of spin sector can be obtained by tuning the boundary conditions in two layers according to $_{\rm t} = \frac{1}{x} = \frac{1}{x}$. The energies of the lowest two states E $_{\rm g}$ and E $_{\rm l}$ change signi cantly with $_{\rm t}$, with variations of the order of the level spacing. At small d and W , E $_{\rm g}$ rst increases as a quadratic function of $_{\rm t}$ until it is energetically favorable for a vortex (through the hole in the torus encircled by the x axis) to enter the system , a typical feature of a super uid state. The disorder averaged super uid density can be calculated as $n_{\rm s} = \frac{1}{2}h\frac{\theta^2 E_{\rm g}}{\theta_{\rm c}^2}$ if θ^{18} .

In Fig. 3, n_s is plotted as a function of d at W = 0.16 for $N_e = 6;8;10$ and 12. The overall behavior agrees with the generalized mean-eld calculation for pure system (our de nition of n_s is twice that of Ref. 8). Naturally, n_s reduces with increasing d, and we de ne the boundary of the super uid state d by $n_s = 0$, e.g. $d_s = 1.2$ for W = 0.16 shown here. The critical d_s is also shown in Fig. 1 as the dashed line. In the strong W case, d_s becomes obviously sm aller than d_c , indicating a super uid state (phase I) to phase II tran-

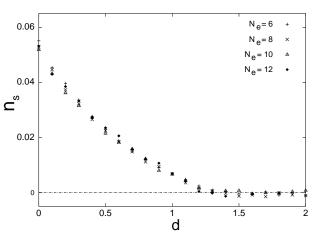


FIG.3: The super uid density n_s vs. d at W = 0.16. At the transition point d_s = 1.2, n_s ! 0.

sition inside the IQHE regime. In phase II, the averaged super uid density vanishes, due principally to phase fustration: $E_g(t)$ still depends strongly upon t with positive or negative curvatures depending on disorder realizations. We postulate hence that the spin sector in phase II behaves as a gauge or vortex glass¹⁹, with Edwards-Anderson magnetic order and algebraic stiness hEg(t = =2) $E_g(t = 0)$ ji L^{j} , as proposed for = 1 bilayers in Ref. 5.

Further evidence that phase II is not a spin insulator is obtained from the spin Chern number C^s, determined by imposing opposite boundary phases to both layers. We nd that C^s uctuates (around 1) throughout the d W plane, implying uidity of the spin sector and a non-quantized spin Hall conductance. This rules out a spin insulator for phase II, favoring the interpretation as a gauge glass. In both phase I and II, the Halldrag conductance $\frac{1}{xy} + \frac{1}{xy} = \frac{1}{2} \begin{pmatrix} c & s \\ xy & xy \end{pmatrix} = (C^{c} C^{s}) \frac{e^{2}}{2h}$, is also non-quantized and non-zero, which is a consequence of the coupling between two layers. At the phase boundary for the IQ HE $(d = d_c)$, we nd that the nondiagonal Chem num ber $C^{1;1} = C^{1;1} = 0$ and the drag H all conductance drops to zero, indicating that the spin sector is also involved in the phase transition at $d = d_c$. At this gauge glass to com posite Ferm i liquid critical point, we expect the spin correlations go from (Edwards-Anderson-) super uid to metallic.

To reveal the charge plateau, we calculate $_{xy}^{c}$ as a function of . Shown in Fig.4, at W = 0.16 and d = 0.8, we observe an exact quantized plateau between = 11=12 = 0.91 and = 13=12 = 1.09, with _{ext} = 0 corresponding to a nitem obility gap. The plateau width is usually smaller or around = 0.2 depending on W, in good agreem ent with experiments²⁰. In contrast to the plateau in charge channel around = 1, the spin Chem number uctuates with di erent disorder con gurations, as shown in the inset of Fig. 4.

We conclude with some comparison to experiments. Both phases I and II exhibit the IQ HE in the charge channel, i.e. $c_{xy}^{c} = h = e^{2}$ and $c_{xx}^{c} = 0$ at zero temperature, and we expect activated corrections at T > 0. The spin C hem

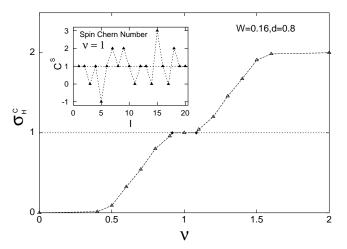


FIG.4: The charge H all conductance $_{xy}^{\circ}$ (in units of $e^2=h$) vs. lling number = N_e=N_s. In the inset, the random spin C hern number C^s vs. disorder con guration I for 20 sam ples at = 1.W = 0:16 and d = 0:8 (in phase I) for both data.

number is random and uctuating, which gives rise to a nonquantized spin conductance. The exact quantized Hallplateau (for the charge) has been observed by several experimental groups^{1,20} with a critical $d_c^{exp} = 1.8$, corresponding to the regime of very weak W 0:07 in our phase diagram . In this regime, the width of phase Π is extrem ely narrow if non-zero, and the Hallplateau phase at $d < d_c$ observed experim entally therefore corresponds to phase I. As a true two-dimensional super uid, it is expected to exhibit anom alous properties, e.g. divergent $_{\mathrm{xx}}^{\mathrm{s}}$ even at non-zero tem peratures below the K osterlitz-Thouless tem perature, T $\,<\,$ T_K $_{\rm T}$. The experim entally observed zero-bias tunneling conductance peak below a characteristic tem perature⁴ is a direct re ection of the associated o -diagonal order in the spin channel. Furtherm ore, the divergent spin conductivity im plies that

the full spin resistivity tensorm ust vanish, $s_{xx} = s_{xy} = 0$ for $T < T_{KT}$. At T = 0, the IQ HE then implies quantized H all drag $d_{xy}^{d} = d_{xy}^{c} = d_{xy}^{s} = h = e^{2}$ and vanishing longitudinal drag, $d_{xx}^{d} = d_{xx}^{c} = d_{xx}^{s} = 0$, in agreem ent with experim ents²⁰. While the quantization of H all drag is expected to be violated for T > 0 by activated processes contributing to $^{\rm c}_{\rm xx}$, the theory predicts that the spin Hall resistivity, should vanish even at non-zero tem perature for $T < T_{K T}$, which would be interesting to explore experim entally. For $d > d_c$, in phase III, we obtain $C^{1;1} = C^{1;1} = 0$ num erically, signaling the decoupling of two layers. As a consequence, the drag conductance and resistance reduce to zero at T = 0, which also agrees with the experim ent^{20} at larger d (d > d_c^{exp}). Lastly, for the relatively pure sample used in Ref20, phase I is directly neighboring phase III which results in $\frac{d}{xx} \in 0$ only along the phase transition line $d = d_c$ at very low tem perature, a property again observed experimentally 20 . For m one disordered samples at interm ediate d, phase Π (gauge glass) intervenes. W hile we expect this phase exhibits the same transport coe cients as phase I at T = 0, it has no associated K osterlitz-T houless transition. This in plies that s_{xy}^{s} ; s_{xx}^{s} are generally non-zero for T > 0 in this range, and probably that $\frac{d}{xx}$ is enhanced at low but non-zero tem peratures. W e leave a more detailed investigation of the gauge glass to a future study.

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